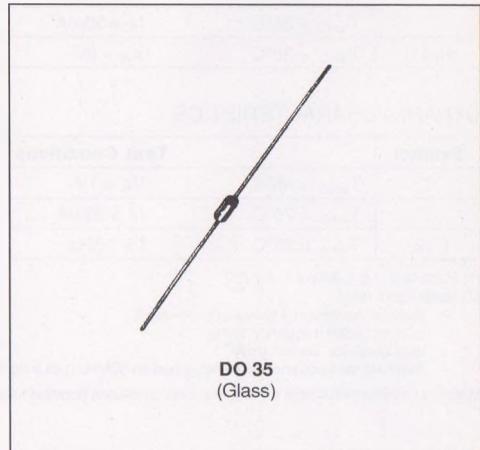


SMALL SIGNAL SCHOTTKY DIODE


DESCRIPTION

Metal to silicon junction diode primarily intended for UHF mixers and ultrafast switching applications.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	15	V
I_F	Forward Continuous Current*	30	mA
I_{FSM}	Surge non Repetitive Forward Current*	60	mA
T_{stg} T_j	Storage and Junction Temperature Range	- 65 to 150 125	°C °C
T_L	Maximum Lead Temperature for Soldering during 10s at 4mm from Case	230	°C

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Junction-ambient*	400	°C/W

* On infinite heatsink with 4mm lead length

ELECTRICAL CHARACTERISTICS**STATIC CHARACTERISTICS**

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
V (BR)	T _{amb} = 25°C	I _R = 10µA	15			V
V _F (1)	T _{amb} = 25°C	I _F = 1mA			0.38	V
	T _{amb} = 25°C	I _F = 10mA			0.5	
	T _{amb} = 25°C	I _F = 30mA			1	
I _R (1)	T _{amb} = 25°C	V _R = 6V			0.1	µA

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
C	T _{amb} = 25°C	V _R = 1V	f = 1MHz			1.1	pF
τ	T _{amb} = 25°C	I _F = 20mA	Krakauer Method			100	ps
F (2)	T _{amb} = 25°C	f = 1GHz			6	7	dB

(1) Pulse test : I₀ ≤ 300µs δ < 2%

(2) Noise figure test :

- diode is inserted in a tuned stripline circuit
- local oscillator frequency 1GHz
- local oscillator power 1mW
- intermediate frequency amplifier, tuned on 30MHz, has a noise figure 1.5dB

Matched batches available on request. Test conditions (forward voltage and/or capacitance) according to customer specification.

